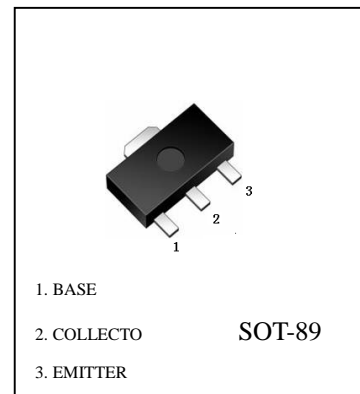


FEATURES

- Large collector power dissipation PC
- Complementary to 2SD874A

Maximum Ratings (Ta=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current -Continuous	I _C	-1	A
Collector Power dissipation	PC	0.5	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55to +150	°C

2SB766A (PNP)


ELECTRICAL CHARACTERISTICS (@ Ta=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _C =-10μA, I _E =0	-60			V
Collector-emitter breakdown voltage	V _{CEO}	I _C =-2mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} =-20V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-10V, I _C =-500mA	85		340	
	h _{FE(2)}	V _{CE} =-5V, I _C =-1A	50			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B =-50mA		-0.2	-0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-500mA, I _B =-50mA		-0.85	-1.2	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-50mA, f=200MHz		200		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		20	30	pF

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	85-170	120-240	170-340
Marking	BQ	BR	BS

2SB766A Typical Characteristics

